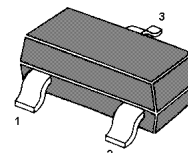
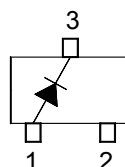


## Silicon Epitaxial Planar Schottky Barrier Diode

For small current rectification and switching applications



Marking Code: **M1M**  
SOT-23 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Average Forward Current	$I_{F(AV)}$	200	mA
Peak Forward Current	$I_{FM}$	300	mA
Non-repetitive Peak Forward Surge Current (10 ms)	$I_{FSM}$	1	A
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	$V_F$	-	0.55	V
Reverse Current at $V_R = 30\text{ V}$	$I_R$	-	50	$\mu\text{A}$
Terminal Capacitance at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	30	-	pF
Reverse Recovery Time at $I_F = I_R = 100\text{ mA}$ , $I_{rr} = 10\text{ mA}$ , $R_L = 100\ \Omega$	$t_{rr}$	3	-	ns



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